Octal D Flip-Flop with Common Clock and Reset

High-Performance Silicon-Gate CMOS

The MC74HC273A is identical in pinout to the LS273. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of eight D flip—flops with common Clock and Reset inputs. Each flip—flop is loaded with a low—to—high transition of the Clock input. Reset is asynchronous and active low.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 264 FETs or 66 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

LOGIC DIAGRAM $\frac{2}{}$ Q0 5 Q1 D2 <u>7</u> 6 Q2 9 DATA Q3 NONINVERTING **INPUTS** 13 12 OUTPUTS Q4 14 15 Q5 17 16 Q6 18 D7 19 CLOCK 11 PIN 20 = V_{CC} RESET 1 PIN 10 = GND

Design Criteria	Value	Units
Internal Gate Count*	66	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рЈ

^{*}Equivalent to a two-input NAND gate.



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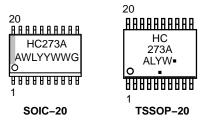
SOIC-20 DW SUFFIX CASE 751D

DT SUFFIX CASE 948E

PIN ASSIGNMENT

R	ESET	1●	20	0		V_{CC}
	Q0	2	19	9		Q7
	D0	3	18	В		D7
	D1	4	17	7	1	D6
	Q1	5	16	6		Q6
	Q2	6	1	5		Q5
	D2	7	14	4		D5
	D3	8	13	3		D4
	Q3	9	12	2	0	Q4
	GND	10	1	1		CLOCK

MARKING DIAGRAMS



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year

WW, W = Work Week
G or ■ = Pb–Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

	Inputs	Output	
Reset	Clock	D	Q
L	Х	Х	L
Н		Н	н
H		L	L
Н	L	X	No Change
Н	~	Х	No Change

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	±20	mA
I _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C

TSSOP Package: -6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parame	Parameter		Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V _{CC}	V
T _A	Operating Temperature, All Package Types	Operating Temperature, All Package Types		+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5	1.5 2.1 3.15	1.5 2.1 3.15	1.5 2.1 3.15	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	6.0 2.0 3.0 4.5 6.0	4.2 0.5 0.9 1.35 1.8	4.2 0.5 0.9 1.35 1.8	4.2 0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{split} V_{in} = V_{IH} & I_{out} \leq 2.4 \text{ n} \\ I_{out} \leq 6.0 \text{ n} \\ I_{out} \leq 7.8 \text{ n} \end{split}$	A 4.5	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V _{OL}	Maximum Low–Level Output Voltage	$ V_{in} = V_{IL} $ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$ \begin{aligned} V_{in} = V_{IL} & I_{out} \leq 2.4 \text{ n} \\ I_{out} \leq 6.0 \text{ n} \\ I_{out} \leq 7.8 \text{ n} \end{aligned} $	A 4.5	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \ pF$, Input $t_f = t_f = 6.0 \ ns$)

			Gu	aranteed Li	mit	
Symbol	Parameter	v _{cc}	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 3.0 4.5 6.0	6.0 15 30 35	5.0 10 24 28	4.0 8.0 20 24	MHz
t _{PLH} t _{PHL}	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	2.0 3.0 4.5 6.0	145 90 29 25	180 120 36 31	220 140 44 38	ns
t _{PHL}	Maximum Propagation Delay, Reset to Q (Figures 2 and 4)	2.0 3.0 4.5 6.0	145 90 29 25	180 120 36 31	220 140 44 38	ns
t _{TLH}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	,	10	10	10	pF

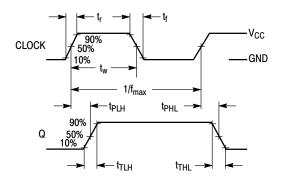
		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Enabled Output)*	48	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

TIMING REQUIREMENTS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

				Guaranteed Limit						
			v _{cc}	–55 to	25°C	≤ 8	5°C	≤ 12	25°C	
Symbol	Parameter	Figure	Volts	Min	Max	Min	Max	Min	Max	Unit
t _{su}	Minimum Setup Time, Data to Clock	3	2.0 3.0 4.5 6.0	60 23 12 10		75 27 15 13		90 32 18 15		ns
t _h	Minimum Hold Time, Clock to Data	3	2.0 3.0 4.5 6.0	3.0 3.0 3.0 3.0		3.0 3.0 3.0 3.0		3.0 3.0 3.0 3.0		ns
t _{rec}	Minimum Recovery Time, Reset Inactive to Clock	2	2.0 3.0 4.5 6.0	5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		ns
t _w	Minimum Pulse Width, Clock	1	2.0 3.0 4.5 6.0	60 23 12 10		75 27 15 13		90 32 18 15		ns
t _w	Minimum Pulse Width, Reset	2	2.0 3.0 4.5 6.0	60 23 12 10		75 27 15 13		90 32 18 15		ns
t _r , t _f	Maximum Input Rise and Fall Times	1	2.0 3.0 4.5 6.0		1000 800 500 400		1000 800 500 400		1000 800 500 400	ns

SWITCHING WAVEFORMS



RESET $t_{\rm W}$ $V_{\rm CC}$ - GND - CLOCK - GND - CLOCK - GND

Figure 1.

Figure 2.

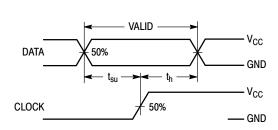
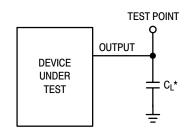


Figure 3.



*Includes all probe and jig capacitance

Figure 4. Test Circuit

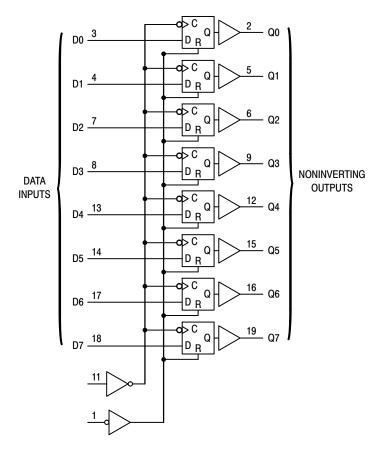


Figure 5. Expanded Logic Diagram

ORDERING INFORMATION

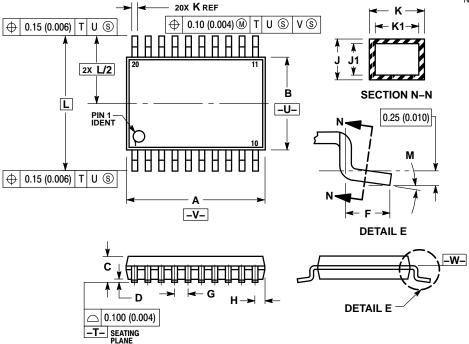
Device	Package	Shipping [†]
MC74HC273ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC273ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC273ADTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74HC273ADTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel
NLV74HC273ADTR2G*	TSSOP-20 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.

PACKAGE DIMENSIONS

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE C**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 - SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE

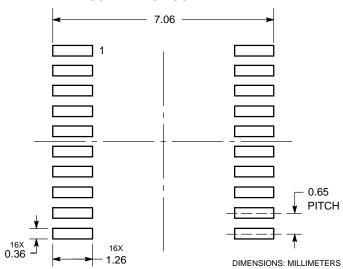
 DAMBAR PROTRUSION. ALLOWABLE

 DAMBAR PROTRUSION SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K

 DIMENSION AT MAXIMUM MATERIAL
 - CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252		
M	0°	8°	0°	8°	

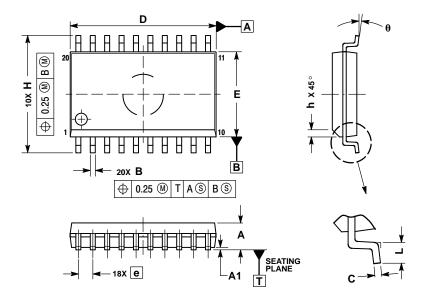
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**



NOTES:

- DIMENSIONS ARE IN MILLIMETERS. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION
 SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
Е	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

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